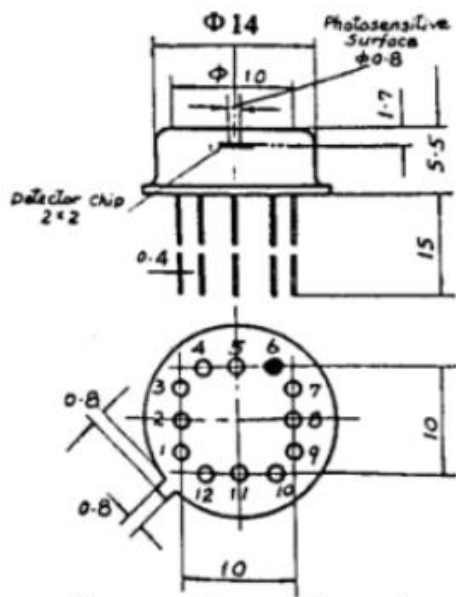


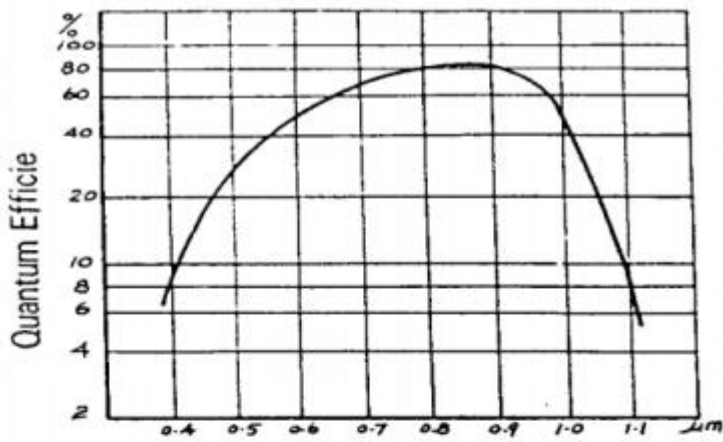
Parameter		Symbol	Unit	Numerical Value			
				Min	Typical	Max.	
1	Photosurface	Diam	Φ	mm		0.8	
		Area	A	mm ²		0.5	
2	Spectral Range			nm	400		1100
3	Dark Current		I_d	nA			200
4	Working Voltage		V_{opt}	V	275		425
5	Operating voltage temperature coefficient		K	V/°C	1.0		2.4
6	Voltage Response	1064nm	R_v	$V/W \times 10^6$	0.6	1.0	
			R_v	$V/W \times 10^6$			
7	Noise equivalent power	1064nm	NEP	PW/Hz ^{1/2}		0.19	0.29
			NEP	PW/Hz ^{1/2}			
8	Response rise time		T_r	ns		7	10
9	Response fall time		T_f	ns		7	10
10	Output Impedance			Ω		25	50
11	Output terminal bias voltage			V	0.0	0.2	1.0
12	Amplifier supply voltage		V_s	V		± 5.0	
13	Amplifier supply current		$+I_s$	mA		20	
14	Amplifier supply current		$-I_s$	mA		10	
15	Maximum reverse dark current		T_a	°C	-40		+70
16	Maximum reverse dark current		I_D	μA			0.2
17	Maximum photocurrent	Average	I_p	mA			2.5
		Peak	I_p	mA			10



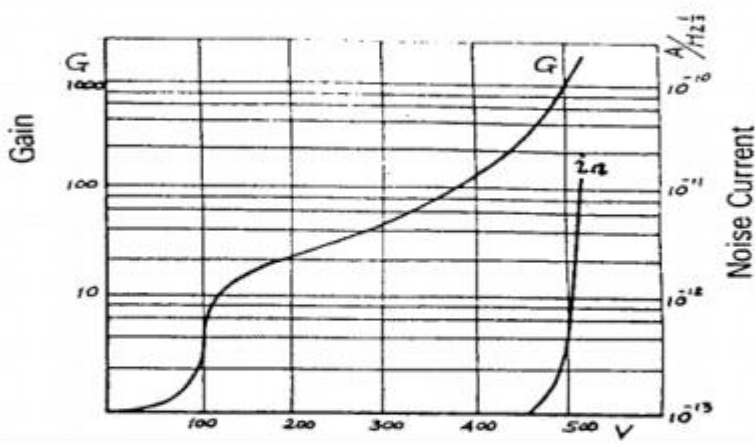
Construction and dimensions

Pin	Join Methods
1	Signal Output
2	—
3	Input Power : -5V
4	APD bias voltage
5	—
6	Pipe shell earthing
7	Load earthing
8	Temperature compensation AD509:anode
9	Temperature compensation AD509:cathode
10	Input Power earthing
11	—
12	Input Power : +5V

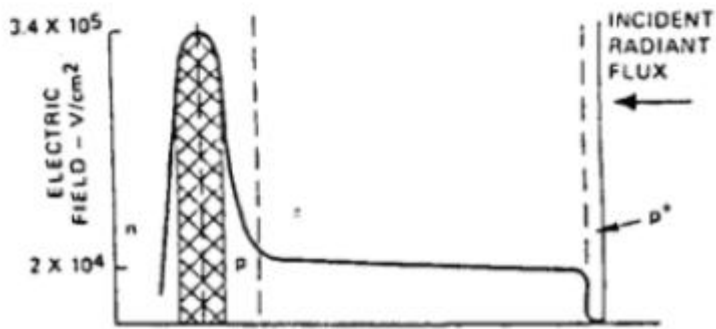
Pin Join Methods



Spectral response curve



$G \sim V_{opt}$, $I_n \sim V_{opt}$ curve



electric-field distribution